

In the Specification:

Please amend the paragraph starting on page 8, line 24 as follows:

~~Fig. 4 is~~ Fig. 5 is a graph illustrating a thickness of a dielectric film according to a deposition thickness of a thin film having a high dielectric constant.

Please amend the paragraph starting on page 12, line 7 as follows:

Preferably, the Al-rich $\text{HfO}_2\text{-Al}_2\text{O}_3$ film 47 and the Hf-rich $\text{HfO}_2\text{-Al}_2\text{O}_3$ film 49 have a thickness ranging from 5 to 30Å and 10 to 100Å, respectively, and formed according to an ALD process. Specifically, the ALD process is performed at a temperature ranging from 150 to 600°C using $\text{Al}(\text{CH}_3)_3$ ~~$\text{Al}(\text{CH}_3)_3$~~ as an Al source, HfCl_4 as a Hf source and H_2O as an O source. One cycle of Al_2O_3 comprises Al pulse, N_2 purge, H_2O pulse and N_2 purge processes, and one cycle of HfO_2 comprises Hf pulse, N_2 purge, H_2O pulse and N_2 purge processes.

Please amend the paragraph starting on page 12, line 16 as follows:

In addition, the Hf source may be selected from the group consisting of HfCl_4 , $\text{Hf}[\text{N}(\text{C}_2\text{H}_5)_2]_4$, $\text{Hf}[\text{N}(\text{CH}_3)_2]_4$ ~~$\text{Hf}[\text{N}(\text{CH}_3)_2]_4$~~ , $\text{Hf}[\text{N}(\text{CH}_3)(\text{C}_2\text{H}_5)]_4$, $\text{Hf}[\text{OC}(\text{CH}_3)_3]_4$, $\text{Hf}(\text{NO}_3)_4$, and combinations thereof, the O source may be selected from the group consisting of H_2O , O_2 , N_2O , O_3 , and combinations thereof, and one cycle of HfO_2 may comprise Hf pulse, N_2 purge, O pulse and N_2 purge.

Please amend the paragraph starting on page 13, line 15 as follows:

~~Fig. 4 is~~ Fig. 5 is a graph illustrating a thickness of the dielectric films according to a deposition thickness of a thin film of the present invention and the conventional arts. As shown in ~~Fig. 4~~ Fig. 5, the $\text{HfO}_2\text{-Al}_2\text{O}_3$ film of the invention has a smaller thickness.